MCH6320

Power MOSFET -12V, 70mΩ, -3.5A, Single P-Channel



www.onsemi.com

Features

- 1.8V Drive
- High Speed Switching
- Pb-Free and RoHS Compliance

VDSS	R _{DS} (on) Max	ID Max
	70mΩ@ –4.5V	
-12V	115mΩ@ –2.5V	-3.5A
	215mΩ@ –1.8V	

Specifications

Absolute Maximum Ratings at Ta = 25°C

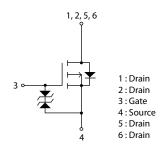
Parameter	Symbol	Value	Unit
Drain to Source Voltage	V _{DSS}	-12	V
Gate to Source Voltage	VGSS	±10	V
Drain Current (DC)	ID	-3.5	Α
Drain Current (Pulse) PW≤10μs, duty cycle≤1%	I _{DP}	-14	А
Power Dissipation When mounted on ceramic substrate (1200mm² × 0.8mm)	PD	1.5	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55 to +150	°C

This product is designed to "ESD immunity < 200V*", so please take care when handling.

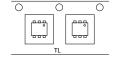
Thermal Resistance Ratings

Parameter	Symbol	Value	Unit
Junction to Ambient When mounted on ceramic substrate (1200mm ² × 0.8mm)	R _{θJA}	83.3	°C/W

Electrical Connection P-Channel



Packing Type: TL Marking





Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

^{*} Machine Model

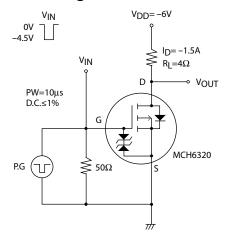
MCH6320

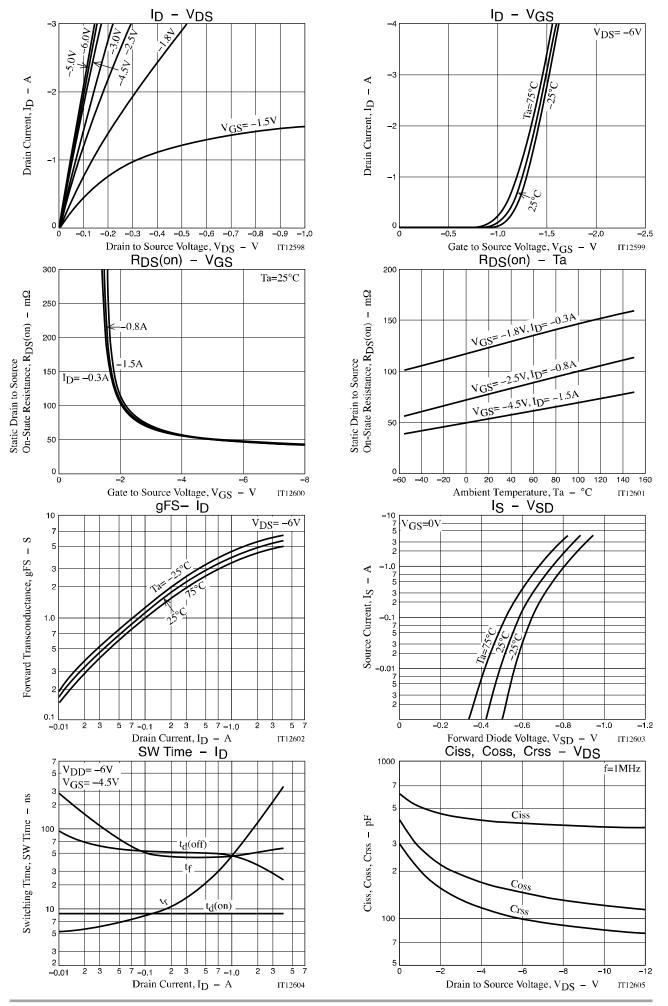
Electrical Characteristics at Ta = 25°C

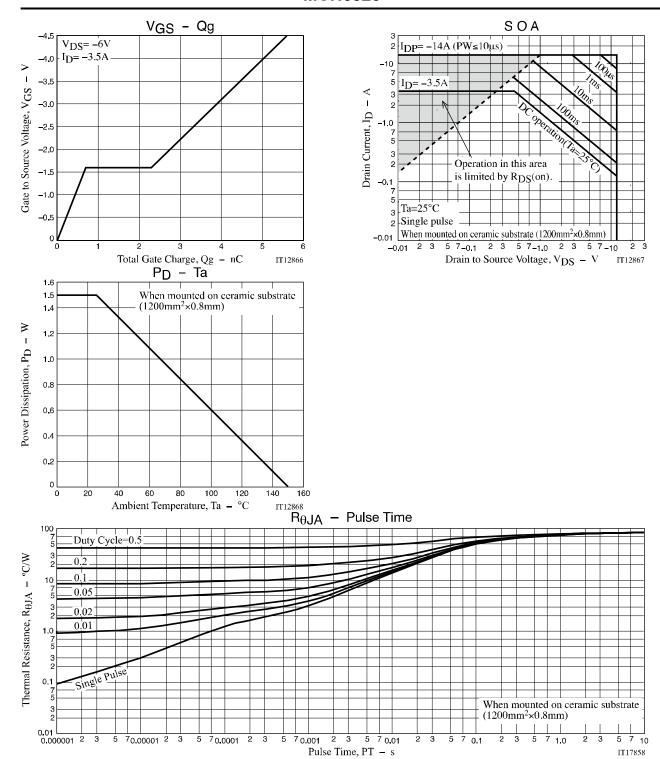
Parameter	Symbol	Conditions	Value			11.2
			min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	I _D =-1mA, V _{GS} =0V	-12			٧
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =-12V, V _{GS} =0V			-10	μΑ
Gate to Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0V			±10	μΑ
Gate Threshold Voltage	V _{GS} (th)	V _{DS} =-6V, I _D =-1mA	-0.4		-1.4	V
Forward Transconductance	9FS	V _{DS} =-6V, I _D =-1.5A	2.7	4.5		S
Static Drain to Source On-State Resistance	R _{DS} (on)1	I _D =-1.5A, V _{GS} =-4.5V		54	70	mΩ
	R _{DS} (on)2	I _D =-0.8A, V _{GS} =-2.5V		80	115	mΩ
	R _{DS} (on)3	I _D =-0.3A, V _{GS} =-1.8V		125	215	mΩ
Input Capacitance	Ciss			405		pF
Output Capacitance	Coss	V _{DS} =–6V, f=1MHz		145		pF
Reverse Transfer Capacitance	Crss			100		pF
Turn-ON Delay Time	t _d (on)			8.8		ns
Rise Time	t _r]		80		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit		41		ns
Fall Time	t _f	1		50		ns
Total Gate Charge	Qg			5.6		nC
Gate to Source Charge	Qgs	V _{DS} =-6V, V _{GS} =-4.5V, I _D =-3.5A		0.7		nC
Gate to Drain "Miller" Charge	Qgd	1		1.6		nC
Forward Diode Voltage	V _{SD}	I _S =-3.5A, V _{GS} =0V		-0.86	-1.2	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Switching Time Test Circuit







Package Dimensions

MCH6320-TL-E / MCH6320-TL-W

МСРН6

CASE 419AS ISSUE O

unit: mm

1: Drain

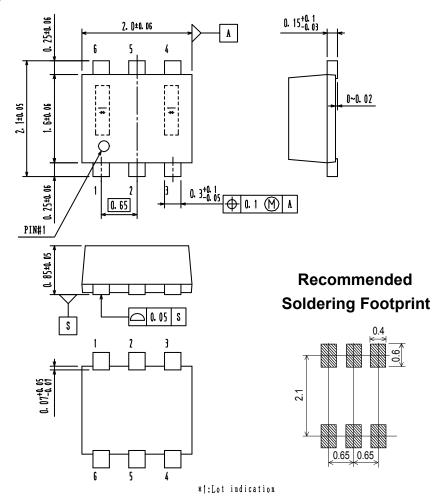
2: Drain

3: Gate

4 : Source

5: Drain

6: Drain



ORDERING INFORMATION

Device	Package	Shipping	Note	
MCH6320-TL-E	MCPH6	0.000 /T 0. Dl	Pb-Free	
MCH6320-TL-W	SC-88FL,SC-70-6,SOT-363	3,000 pcs. / Tape & Reel	Pb-Free and Halogen Free	

[†] For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub_link/Collateral/BRD8011-D.PDF

Note on usage: Since the MCH6320 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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